

Title (en)

PROCESS FOR PRODUCING A P-N JUNCTION IN A CZTS-BASED PHOTOVOLTAIC CELL AND CZTS-BASED SUPERSTRATE PHOTOVOLTAIC CELL

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES P-N-ÜBERGANG IN EINER CZTS-BASIERTEN FOTOVOLTAISCHEN ZELLE UND CZTS-BASIERTE SUPERSTRAT-PV-ZELLE

Title (fr)

PROCÉDÉ DE RÉALISATION D'UNE JONCTION PN DANS UNE CELLULE PHOTOVOLTAÏQUE À BASE DE CZTS ET CELLULE PHOTOVOLTAÏQUE EN CONFIGURATION SUPERSTRAT ET À BASE DE CZTS

Publication

**EP 3028311 A1 20160608 (FR)**

Application

**EP 14767116 A 20140722**

Priority

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- IB 2014063305 W 20140722

Abstract (en)

[origin: WO2015015367A1] The invention relates to a process for producing a p-n junction in a photovoltaic cell made of thin CZTS-based films, comprising: a) a step of depositing a film of precursors containing zinc, tin and copper, the amount of zinc being larger than that required to convert the precursors into a CZTS type photovoltaic material and b) a step of annealing the precursors, under a sulphur- and/or selenium-containing atmosphere, so as to obtain a photovoltaic film made of CZTS and a buffer layer made of ZnS<sub>1-x</sub>Se<sub>x</sub>, where x is comprised between 0 and 1.

IPC 8 full level

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Citation (search report)

See references of WO 2015015367A1

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